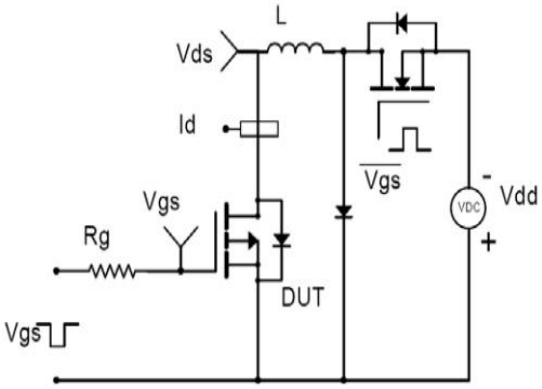
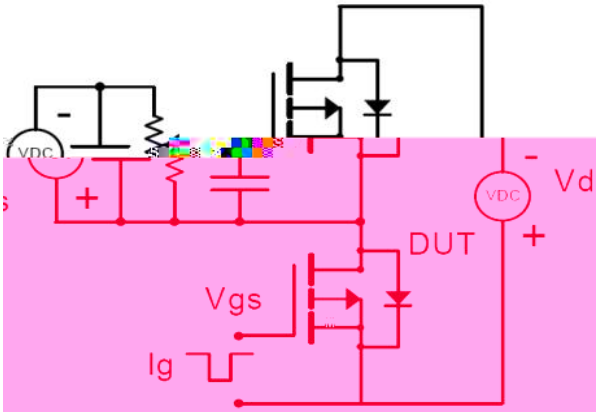
$R_{\theta JA}$	Junction-to-Ambient	—	100	°C/W

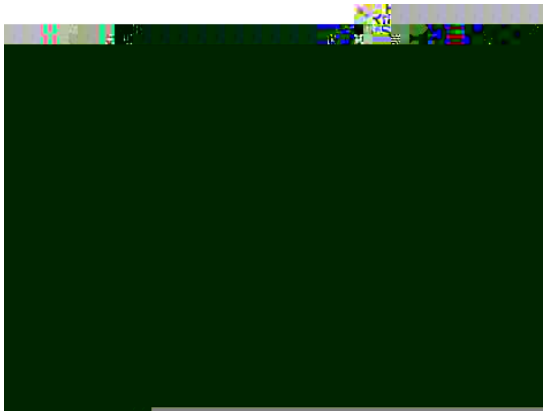
@T_A=25°C unless otherwise specified

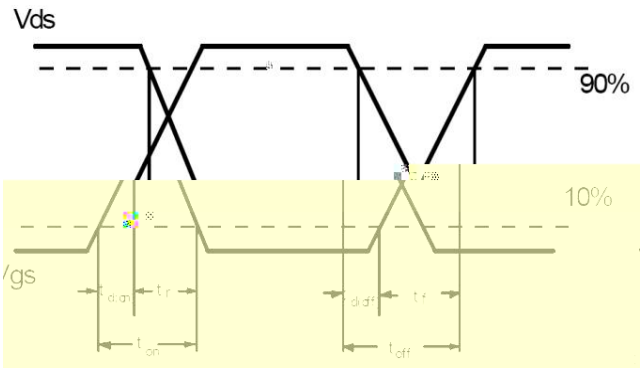
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	-12	—	—	V	V_{GS} = 0V, I_D =-250μA
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	33	50	mΩ	V_{GS}=-4.5V,I_D =-4.4A
		—	48	85	mΩ	V_{GS}=-2.5V,I_D =-3.8A
$V_{GS(th)}$	Gate threshold voltage	-0.4	—	-1	V	V_{DS} = V_{GS}, I_D =-250μA
I_{DSS}	Drain-to-Source leakage current	—	—	-1	μA	V_{DS} =-12V,V_{GS} = 0V
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	V_{GS} =8V
		—	—	-100		V_{GS} = -8V
Q_g	Total gate charge	—	12	—	nC	I_D =-3.5A,
Q_{gs}	Gate-to-Source charge	—	1.5	—		V_{DS}=-8V,
Q_{gd}	Gate-to-Drain("Miller") charge	—	3	—		V_{GS} = -4.5V
$t_{d(on)}$	Turn-on delay time	—	11.3	—	ns	V_{GS}=-10V, V_{DD}=-10V,
t_r	Rise time	—	18.1	—		R_{GEN}=3Ω
$t_{d(off)}$	Turn-Off delay time	—	32.4	—		I_D = -1.0A
t_f	Fall time	—	38.1	—		
C_{iss}	Input capacitance	—	638	—	pF	V_{GS} = 0V
C_{oss}	Output capacitance	—	238	—		V_{DS} = -12V
C_{rss}	Reverse transfer capacitance	—	221	—		f = 1MHz

I_S	Continuous Source Current (Body Diode)	—	—	-3.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	-14	A	
V_{SD}	Diode Forward Voltage	—	-0.8	-1.2	V	I_S=-1.7A, V_{GS}=0V









Calculated continuous current based on maximum allowable junction temperature.

Repetitive rating; pulse width limited by max. junction temperature.

The power dissipation P_D is based on max. junction temperature, using junction-to-case thermal resistance.

The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C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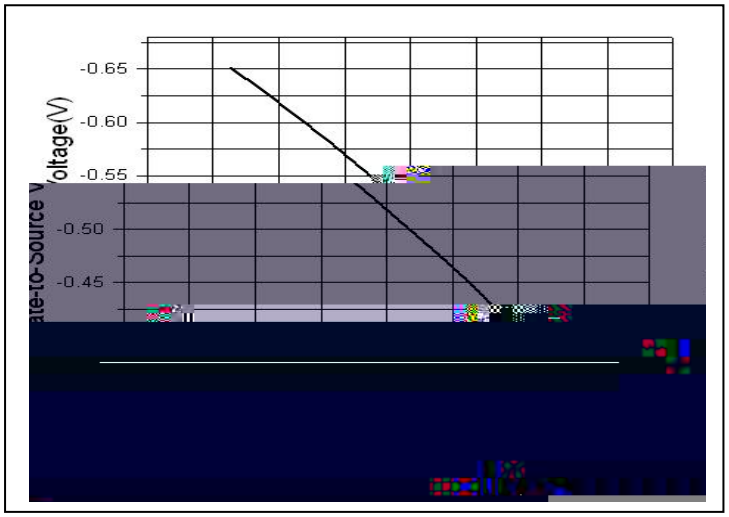
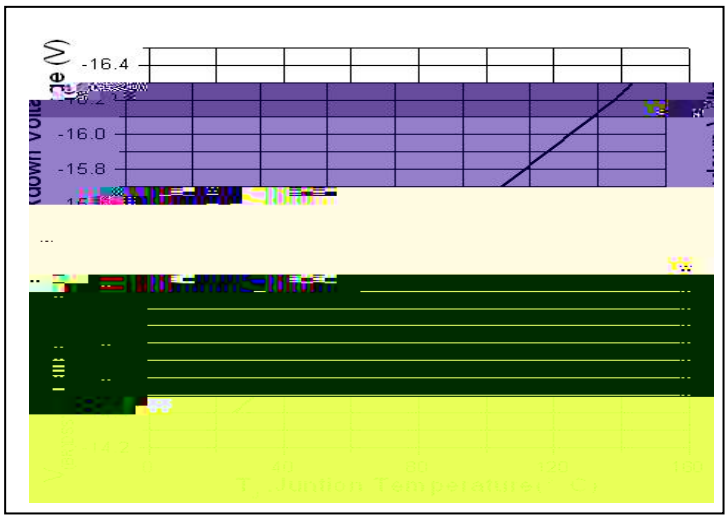
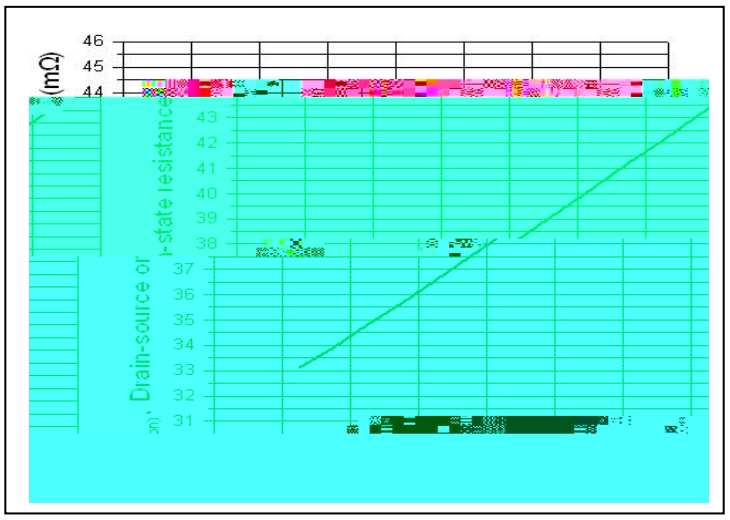

-0.65
-0.60
-0.55
-0.50
-0.45


-16.4
-16.0
-15.8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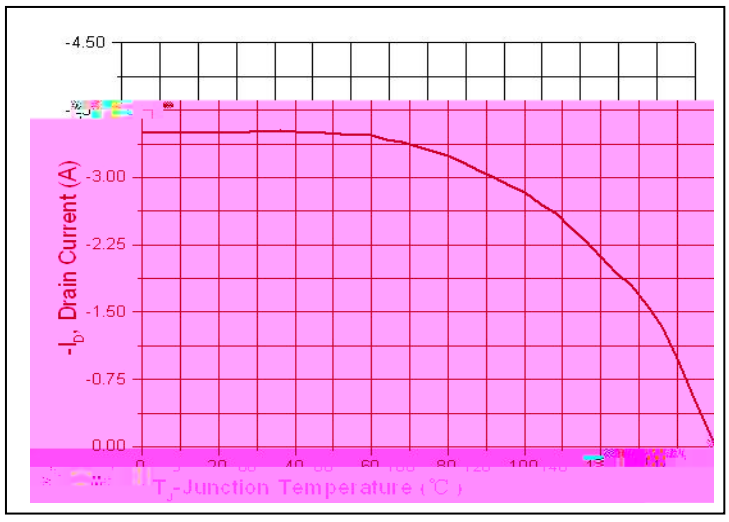
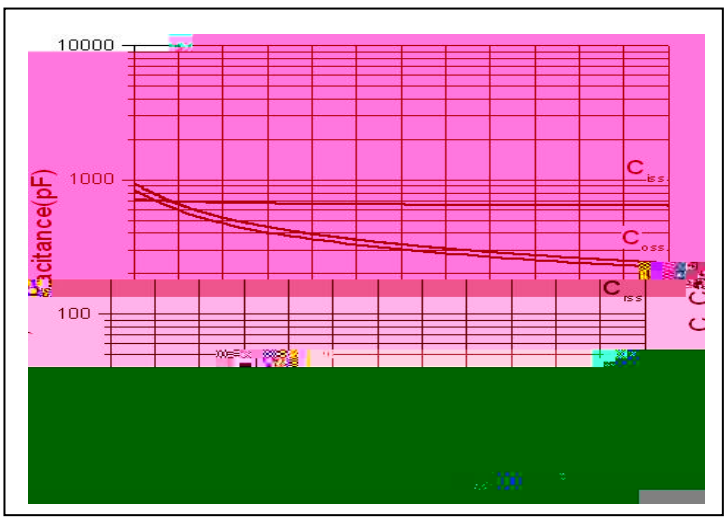
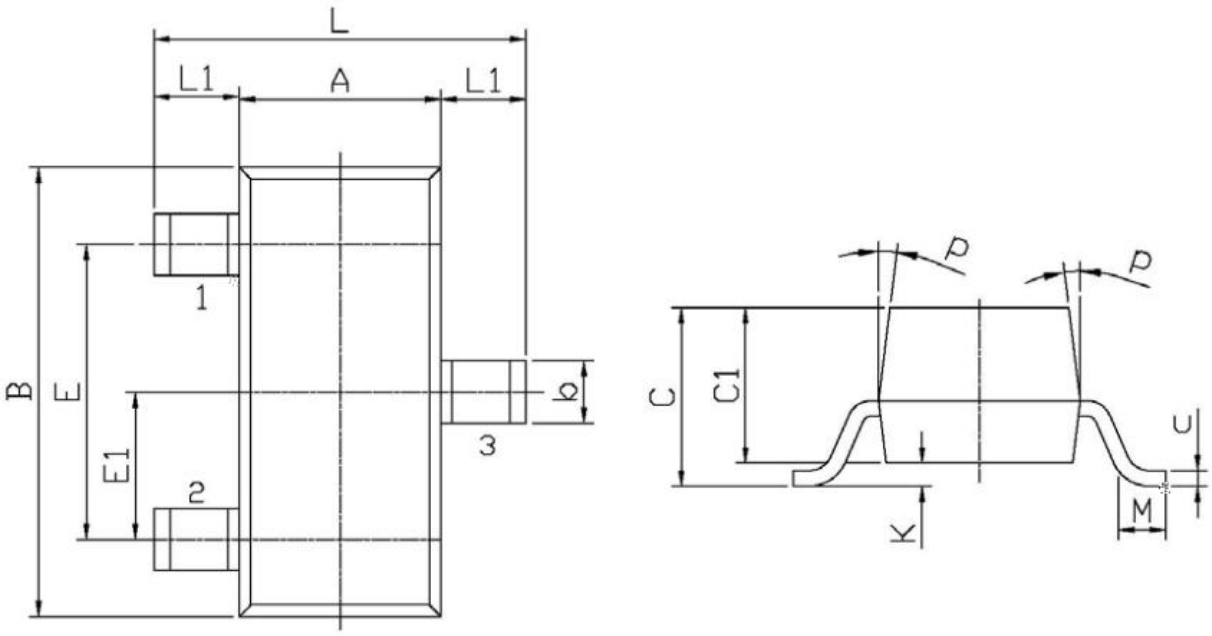

-4.50
-3.00
-2.25
-1.50
-0.75
0.00
$-I_D$, Drain Current (A)
T_j-Junction Temperature (℃)


10000
1000
100
C_{iss}
C_{oss}
C_{rss}



Symbol	Dimensions in Millimeter		Symbol	Dimensions in Millimeter	
	Min	Max		Min	Max
L	2.2	2.7	C	1.30 Max	
L1	0.45	0.65	C1	0.90	1.20
A	1.15	1.50	c	0.05	0.20
B	2.70	3.10	K	0	0.10
E	1.70	2.10	M	0.20 Min	
E1	0.85	1.05	P	7º	
b	0.35	0.55			

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